AMENDMENTS TO THE SPECIFICATION:

Please replace paragraph [0012] with the following rewritten paragraph:

--It is another object of the present invention to provide a SiCOH dielectric material having a dielectric constant of not more than 2.8, which is very stable towards ~~H2O~~ H_2O vapor (humidity) exposure, including a resistance to crack formation in water.--

Please replace paragraph [0019] with the following rewritten paragraph:

--In a fourth embodiment of the present invention, a stable ultra low k SiCOH dielectric material that has a dielectric constant of 2.4, a tensile stress of less than 40 MPa, an elastic modulus from about 6 to about 11 GPa, and a hardness from about 0.3 to about 1.7 GPa is provided. A cohesive strength from about 2.4 to about 3.8 ~~J/m2~~ J/m^2, and a crack development velocity in water of not more than 1x10-10 m/sec for a film thickness of 2.3 microns is provided by the dielectric material of the fourth embodiment of the present invention.--

Please replace paragraph [0020] with the following rewritten paragraph:

-- In a fifth embodiment of the present invention, a stable ultra low k SiCOH dielectric material that has a dielectric constant of 2.3, a tensile stress of less than 40 MPa, an elastic modulus from about 5 to about 10 GPa, and a hardness from about 0.25 to about 1.6 GPa is provided. Dielectric material within the fifth embodiment of the present invention has a cohesive strength from about 2.2 to about 3.7 ~~J/m2~~ J/m^2, and a crack development velocity in water of not more than 1x10-10 m/sec for a film thickness of 1.9 microns is provided.--

Please replace paragraph [0021] with the following rewritten paragraph:

--In a sixth embodiment of the present invention, a stable ultra low k SiCOH dielectric material that has a dielectric constant of 2.2, a tensile stress of less than 40 MPa, an elastic modulus from about 4 to about 9 GPa, and a hardness from about 0.2 to about 1.5 GPa is

provided. The SiCOH dielectric material of the sixth embodiment has a cohesive strength from about 2.0 to about 3.5 ~~J/m2~~ J/m^2, and a crack development velocity in water of not more than 1x10-10 m/sec for a film thickness of 1.5 microns.--

Please replace paragraph [0022] with the following rewritten paragraph:

--In a seventh embodiment of the present invention, a stable ultra low k SiCOH dielectric material that has a dielectric constant of 2.1, a tensile stress from about 20 to about 35 MPa, an elastic modulus from about 3 to about 8 GPa, and a hardness from about 0.2 to about 1.4 GPa is provided. In this embodiment of the present invention, the SiCOH dielectric material has a cohesive strength from about 1.8 to about 3.4 ~~J/m2~~ J/m^2, and a crack development velocity in water of not more than 1x10-10 m/sec for a film thickness of 1.3 microns.--